#### PATENT APPLICATION

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q80166

Masato KOBAYAKAWA, et al.

Appln. No.: 10/589,610

Group Art Unit: 2811

Confirmation No.: 8635

Examiner: Unknown

Filed: August 16, 2006

For:

GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR MULTILAYER

STRUCTURE AND PRODUCTION METHOD THEREOF

## REQUEST FOR CORRECTED OFFICIAL FILING RECEIPT

ATTN: Office of Initial Patent Examination

Filing Receipt Correction Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

We enclose a copy of the Official Filing Receipt for the above-identified application and request the following correction:

## **Assignment for Published Patent Application**

SHOWA DENKO K.K., Minato-ku, Tokyo, JAPAN SHOWA DENKO K.K.

Verification for the requested correction is indicated on the Executed Assignment Document filed August 16, 2006.

Respectfully submitted,

Abraham J. Rosner

Registration No. 33,276

SUGHRUE MION, PLLC

Telephone: (202) 293-7060

Facsimile: (202) 293-7860

WASHINGTON OFFICE

23373

CUSTOMER NUMBER

Date: May 9, 2007



## UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address COMMISSIONER FOR PATENTS FO. Box 1450 Alexandria, Virginia 22313-1450

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**CONFIRMATION NO. 8635** 

23373
SUGHRUE MION, PLLC
2100 PENNSYLVANIA AVENUE, N.W. DOCKETED
SUITE 800
WASHINGTON, DC 20037

APR 18 2007

FILING RECEIPT
\*OC000000023387955\*

Date Mailed: 04/16/2007

Receipt is acknowledged of this regular Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please mail to the Commissioner for Patents P.O. Box 1450 Alexandria Va 22313-1450. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

#### Applicant(s)

Masato Kobayakawa, Chiba, JAPAN; Hitoshi Takeda, Chiba, JAPAN; Hisayuki Miki, Chiba, JAPAN; Tetsuo Sakurai, Chiba, JAPAN;

**Assignment For Published Patent Application** 

SHOWA DENKO K.K., Minato-Ku, Tokyo, JAPAN

SHOWA DENKO K.K.

Power of Attorney: The patent practitioners associated with Customer Number 23373.

#### Domestic Priority data as claimed by applicant

This application is a 371 of PCT/JP05/03428 02/23/2005 which claims benefit of 60/549.440 03/03/2004

### Foreign Applications

JAPAN 2004-048500 02/24/2004

If Required, Foreign Filing License Granted: 04/13/2007

The country code and number of your priority application, to be used for filing abroad under the Paris Convention, is US10/589.610

Projected Publication Date: 07/26/2007

# U.S. ASSIGNMENT

IN CONSIDERATION of the sum of One Dollar (\$1.00), and of other good and valuable consideration paid to the undersigned inventor(s) (hereinafter "ASSIGNOR") by

(Insert	SHOWA DENKO K.K.			
ASSIGNEE's Name(s) Address(es))	13-9, Shibadaimon 1-chome, Minato-ku, Tokyo 105-8518, Japan			
		t of which is bereby acknowledged, the un l exclusive right, title and interest to the i	dersigned ASSIGNOR hereby sells, assi	gus and
(Title of Invention)	GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR MULTILAYER STRUCTURE			
	AND PRODUCTION METHOD THEREOF			
	relating to International Patent Applic of the United States was executed on o	ation PCT/IP 2005 / 003428 even date herewith or, if not so executed.	_and/or for which application for Letter was:	s Pater
(Insert date of execution of application, if not concurrent)	(a) executed on	_: [		]
	(b) filed on Serial No.	data, when known.	authorized to insert in (b) the specified	
	renewal, substitute, reissue or repxami	nation application based thereon, for the	a said application and any continuation, full term or terms for which the said Le cinafter, "said application(s) and Letters	tters
	The ASSIGNOR agree(s), when requested by said ASSIGNEE and without charge to but at the expense of said ASSIGNEE, to do all acts which the ASSIGNEE may deem accessary, desirable or expedient, for securing, maintaining and enforcing protection for said invention, including in the preparation and prosecution of said application(s) and the issuance of said Letters Patent(s), in any interference, reissue, reexamination, or public use proceeding, and in any litigation or other legal proceeding which may arise or be declared in relation to same, such acts to include but not be limited to executing all papers, including separate assignments and declarations, taking all rightful oaths, providing sworm testimony, and obtaining and producing evidence.			
	IN WITNESS WHEREOF,	the undersigned inventor(s) has (have) a	ffixed his/her/their signature(s).	
{Signalures}	"MASATO KOBAYAKAL	Masato Kobayakawa	June 28, 2006	•
	[SIGNATURE]	(EMAN BYYT)	(OATE)	
	21 Hitoshi Takeda	Hitoshi Takeda	June 28, 2006	
	(SIGNATURE)	(TYPE NAME)	(DATE)	
	31 HISAYWC Milci	Hisayuki Miki	June 28, 2006	
	SIGNATURE  STETSTO SARAVAC	Tetsuo Sakurai		
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